

isc Silicon NPN Power Transistor

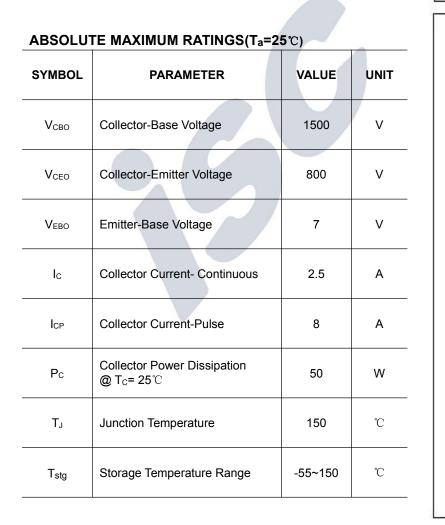
2SD1338

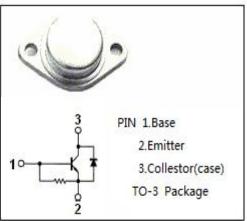
DESCRIPTION

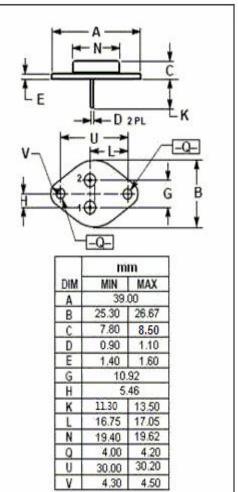
- High Breakdown Voltage-
 - : V_{CBO}= 1500V (Min)
- High Switching Speed
- Built-in Damper Diode
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

· Designed for horizontal output applications.









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ELECTRICAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	МАХ	UNIT
V _{(BR)CBO}	Collector-Base Breakdown Voltage	I _C = 5mA; I _E = 0	1500			V
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = 10mA; R _{BE} = ∞	800			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = 200mA; I _C = 0	7			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 2A; I _B = 0.4A			5.0	V
V _{BE} (sat)	Base-Emitter Saturation Voltage	I _C = 2A; I _B = 0.4A			1.5	V
I _{CBO}	Collector Cutoff Current	V _{CB} = 800V; I _E = 0			10	μA
I _{EBO}	Emitter Cutoff Current	V _{EB} = 4V; I _C = 0	40		130	mA
h _{FE}	DC Current Gain	I _C = 0.5A; V _{CE} = 5V	8			
V _{ECF}	C-E Diode Forward Voltage	I _F = 2.5A			2.0	V

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